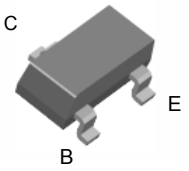
ON Semiconductor®

FSB560 / FSB560A
NPN Low-Saturation Transistor

Features

- These devices are designed with high-current gain and low-saturation voltage with collector currents up to 2 A continuous.



SuperSOT™-3 (SOT-23)

Ordering Information

Part Number	Marking	Package	Packing Method
FSB560	560	SSOT 3L	Tape and Reel
FSB560A	560A	SSOT 3L	Tape and Reel

Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	60	V
V_{CBO}	Collector-Base Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current - Continuous	2	A
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Notes:

1. These ratings are based on a maximum junction temperature of 150°C.
2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

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Publication Order Number:
FSB560A/D

Thermal Characteristics[3]

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Max.	Unit
P_D	Total Device Dissipation	500	mW
	Derate Above 25°C	4	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	250	°C/W

Note:

3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions		Min.	Max.	Unit
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 10 mA, I_B = 0		60		V
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 100 μA, I_E = 0		80		V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 100 μA, I_C = 0		5		V
I_{CBO}	Collector Cut-Off Current	V_{CB} = 30 V, I_E = 0			100	nA
		V_{CB} = 30 V, I_E = 0, T_A = 100°C			10	μA
I_{EBO}	Emitter Cut-Off Current	V_{EB} = 4 V, I_C = 0			100	nA
h_{FE}	DC Current Gain[4]	I_C = 100 mA, V_{CE} = 2 V		70		
		I_C = 500 mA, V_{CE} = 2 V	FSB560	100	300	
			FSB560A	250	550	
		I_C = 1 A, V_{CE} = 2 V		80		
		I_C = 2 A, V_{CE} = 2 V		40		
V_{CE}(sat)	Collector-Emitter Saturation Voltage[4]	I_C = 1 A, I_B = 100 mA			300	mV
		I_C = 2 A, I_B = 200 mA	FSB560		350	
			FSB560A		300	
V_{BE}(sat)	Base-Emitter Saturation Voltage[4]	I_C = 1 A, I_B = 100 mA			1.25	V
V_{BE}(on)	Base-Emitter On Voltage[4]	I_C = 1 A, V_{CE} = 2 V			1	V
C_{obo}	Output Capacitance	V_{CB} = 10 V, I_E = 0, f = 1.0 MHz			30	pF
f_T	Transition Frequency	I_C = 100 mA, V_{CE} = 5 V, f = 100 MHz		75		MHz

Note:

4. Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2.0%

Typical Performance Characteristics

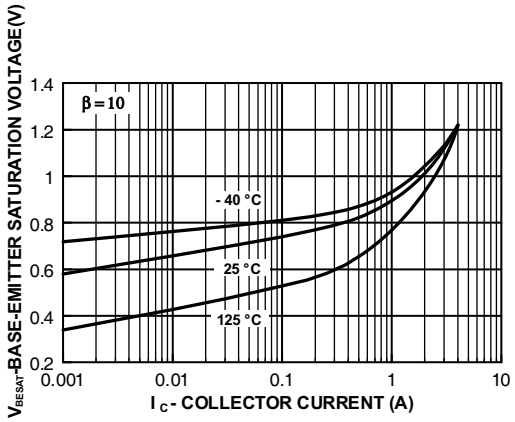


Figure 1. Base-Emitter Saturation Voltage vs. Collector Current

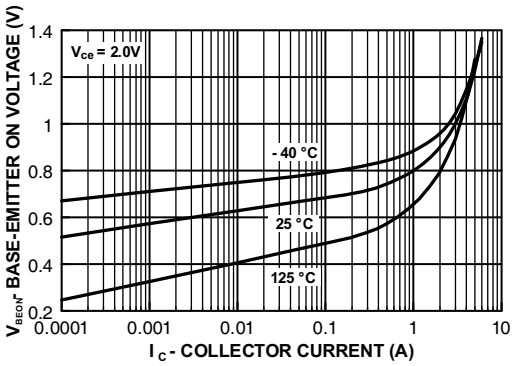


Figure 2. Base-Emitter On Voltage vs. Collector Current

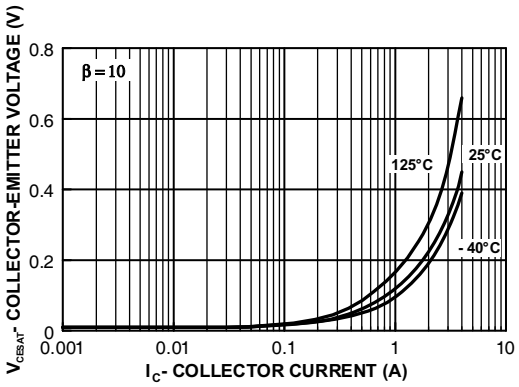


Figure 3. Collector-Emitter Saturation Voltage vs. Collector Current

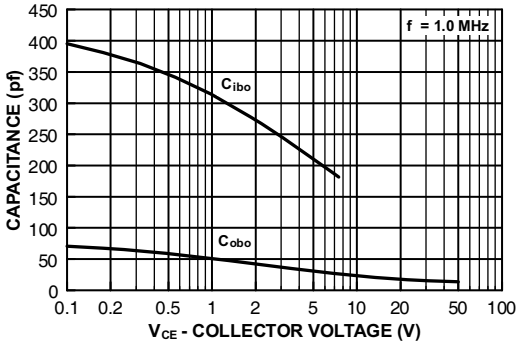


Figure 4. Input / Output Capacitance vs. Reverse Bias Voltage

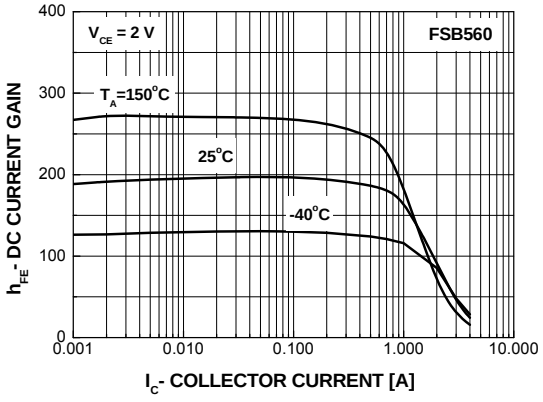


Figure 5. Current Gain vs. Collector Current

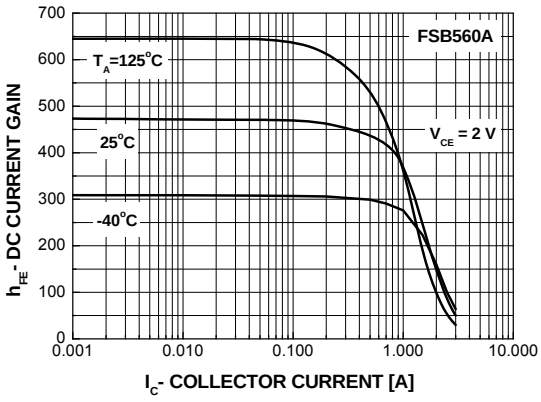


Figure 6. Current Gain vs. Collector Current

Physical Dimensions

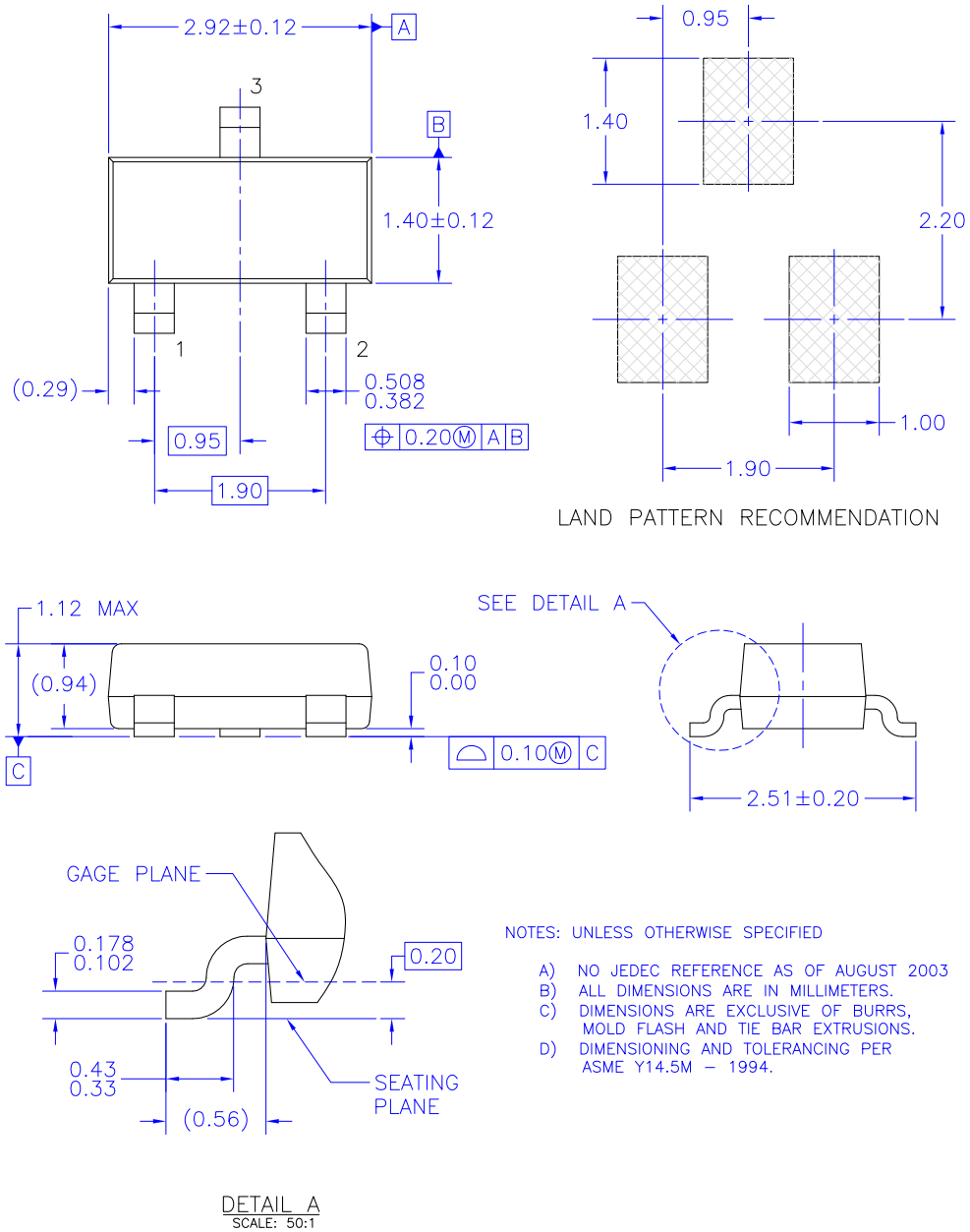


Figure 7. MOLDED PACKAGE, SUPERSOT, 3-LEAD

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